Alan C Seabaugh

List of Publications by Year
in descending order

214 papers	10,972 citations	71102 41 h-index	32842 100 g-index
217 all docs	217 docs citations	217 times ranked	11575 citing authors

#	Article	IF	Citations
1	Mark A. Reed (1955â€“2021). Nature Nanotechnology, 2022, , .	31.5	0
2	Electrical Properties of 6Ânm to 19Ânm Thick Polyethylene Oxide Capacitors for Ion/Electron Functional Devices. Journal of Electronic Materials, 2021, 50, 2956-2963.	2.2	1
3	Electric-double-layer pâ€“iâ€“n junctions in WSe2. Scientific Reports, 2020, 10, 12890.	3.3	4
4	Programming-Pulse Dependence of Ferroelectric Partial Polarization: Insights From a Comparative Study of PZT and HZO Capacitors. IEEE Transactions on Electron Devices, 2020, 67, 4482-4487.	3.0	7
5	Batch-Fabricated WSeâ„‚-on-Sapphire Field-Effect Transistors Grown by Chemical Vapor Deposition. IEEE Transactions on Electron Devices, 2020, 67, 1839-1844.	3.0	5
6	Gallium nitride tunneling field-effect transistors exploiting polarization fields. Applied Physics Letters, 2020, 116, .	3.3	7
7	Quantitative, experimentally-validated, model of MoS2 nanoribbon Schottky field-effect transistors from subthreshold to saturation. Journal of Applied Physics, 2020, 127, .	2.5	5
8	A Device Non-Ideality Resilient Approach for Mapping Neural Networks to Crossbar Arrays. , 2020, , .		3
9	Resolution enhancement of transmission electron microscopy by super-resolution radial fluctuations. Applied Physics Letters, 2020, 116, 044105.	3.3	0
10	Monte Carlo Simulation of Switching Dynamics in Polycrystalline Ferroelectric Capacitors. IEEE Transactions on Electron Devices, 2019, 66, 3527-3534.	3.0	39
11	Room-Temperature Graphene-Nanoribbon Tunneling Field-Effect Transistors. Npj 2D Materials and Applications, 2019, 3, .	7.9	26
12	Two-dimensional electric-double-layer Esaki diode. Npj 2D Materials and Applications, 2019, 3, .	7.9	27
13	Process Dependent Switching Dynamics of Ferroelectric Hafnium Zirconate. , 2019, , .		3
14	Dynamics of Ferroelectric and Ionic Memories: Physics and Applications. , 2019, , .		0
15	Alloy Engineered Nitride Tunneling Field-Effect Transistor: A Solution for the Challenge of Heterojunction TFETs. IEEE Transactions on Electron Devices, 2019, 66, 736-742.	3.0	16
16	Tunnel FET Analog Benchmarking and Circuit Design. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2018, 4, 19-25.	1.5	13
17	Improvement of Metal-Semiconductor Contact from Schottky to Ohmic by Cu Doping in Transition Metal Dichalcogenide Transistors. , 2018, , .		0
18	Experimentally Validated, Predictive Monte Carlo Modeling of Ferroelectric Dynamics and Variability. , 2018, , .		14

#	Article	IF	Citations
19	Using Ions to Control Transport in Two-Dimensional Materials for Ion-Controlled Electronics. , 2018, , .		0
20	Pulse Dynamics of Electric Double Layer Formation on All-Solid-State Graphene Field-Effect Transistors. ACS Applied Materials & Interfaces, 2018, 10, 43166-43176.	8.0	25
21	Electric Double Layer Esaki Tunnel Junction in a 40-nm-Length, WSe2 Channel Grown by Molecular Beam Epitaxy on Al203. , 2018, , .		3
22	Switching Dynamics of Ferroelectric Zr-Doped HfO₂. IEEE Electron Device Letters, 2018, 39, 1780-1783.	3.9	75
23	Multiwall MoS2 tubes as optical resonators. Applied Physics Letters, 2018, 113, .	3.3	30
24	Energetics of metal ion adsorption on and diffusion through crown ethers: First principles study on two-dimensional electrolyte. Solid State Ionics, 2017, 301, 176-181.	2.7	9
25	Monolayer Solid-State Electrolyte for Electric Double Layer Gating of Graphene Field-Effect Transistors. ACS Nano, 2017, 11, 5453-5464.	14.6	40
26	In Quest of the Next Information Processing Substrate. , 2017, , .		0
27	Electric Double Layer Dynamics in Poly(ethylene oxide) LiClO₄ on Graphene Transistors. Journal of Physical Chemistry C, 2017, 121, 16996-17004.	3.1	24
28	First synthesized WS<inf>2</inf> nanotube and nanoribbon field effect transistors grown by chemical vapor transport. , 2017, , .		1
29	Reconfigurable Electric Double Layer Doping in an MoS₂Nanoribbon Transistor. IEEE Transactions on Electron Devices, 2017, 64, 5217-5222.	3.0	9
30	Projected performance of experimental InAs/GaAsSb/GaSb TFET as millimeter-wave detector. , 2017, , .		0
31	Partial switching of ferroelectrics for synaptic weight storage. , 2017, , .		7
32	Atomic Layer Deposition of Al₂O₃ on WSe₂ Functionalized by Titanyl Phthalocyanine. ACS Nano, 2016, 10, 6888-6896.	14.6	69
33	Gate-Controlled WSe2 Transistors Using a Buried Triple-Gate Structure. Nanoscale Research Letters, 2016, 11, 512.	5.7	22
34	Universal charge-conserving TFET SPICE model incorporating gate current and noise. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2016, , 1-1.	1.5	16
35	Electric-double-layer doping of WSe2 field-effect transistors using polyethylene-oxide cesium perchlorate. Journal of Applied Physics, 2016, 120, .	2.5	20
36	Demonstration of electric double layer p-i-n junction in WSe<inf>2</inf>. , 2016, , .		2

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37	Hybrid phase-change â€" Tunnel FET (PC-TFET) switch with subthreshold swing < 10mV/decade and sub-0.1 body factor: Digital and analog benchmarking. , 2016, , .		13
38	Steep slope transistors: Tunnel FETs and beyond. , 2016, , .		16
39	Record high current density and low contact resistance in MoS2 FETs by ion doping. , 2016, , .		6
40	Reconfigurable p-n junction formation and bandgap opening in bilayer graphene using polyethylene oxide and CsClO<inf>4</inf> solid polymer electrolyte. , 2015, , .		1
41	Steep subthreshold swing tunnel FETs: GaN/InN/GaN and transition metal dichalcogenide channels. , 2015, , .		18
42	Low-leakage WSe<inf>2</inf> FET gate-stack using titanyl phthalocyanine seeding layer for atomic layer deposition of Al<inf>2</inf>O<inf>3</inf>. , 2015, , .		3
43	Synthesized multiwall MoS2 nanotube and nanoribbon field-effect transistors. Applied Physics Letters, 2015, 106, .	3.3	66
44	Graphene nanoribbon field-effect transistors on wafer-scale epitaxial graphene on SiC substrates. APL Materials, 2015, 3, .	5.1	72
45	Universal analytic model for tunnel FET circuit simulation. Solid-State Electronics, 2015, 108, 110-117.	1.4	81
46	Reconfigurable Ion Gating of 2H-MoTe₂ Field-Effect Transistors Using Poly(ethylene) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	14.6	110
47	Foreword Special Issue on Transistors With Steep Subthreshold Swing for Low-Power Electronics. IEEE Journal of the Electron Devices Society, 2015, 3, 86-87.	2.1	0
48	Ultimate thin vertical pâ€"n junction composed of two-dimensional layered molybdenum disulfide. Nature Communications, 2015, 6, 6564.	12.8	285
49	Polarization-Engineered III-Nitride Heterojunction Tunnel Field-Effect Transistors. IEEE Journal on Exploratory Solid-State Computational Devices and Circuits, 2015, 1, 28-34.	1.5	73
50	Quantum Transport in AlGaSb/InAs TFETs With Gate Field In-Line With Tunneling Direction. IEEE Transactions on Electron Devices, 2015, 62, 2445-2449.	3.0	11
51	First-Principles Study of Crown Ether and Crown Ether-Li Complex Interactions with Graphene. Journal of Physical Chemistry C, 2015, 119, 20016-20022.	3.1	11
52	Solution-Cast Monolayers of Cobalt Crown Ether Phthalocyanine on Highly Ordered Pyrolytic Graphite. Journal of Physical Chemistry C, 2015, 119, 21992-22000.	3.1	9
53	Tunnel field-effect transistors - update. , 2014, , .		1
54	Electron transport in 2D crystal semiconductors and their device applications. , 2014, , .		2

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55	Vertical heterojunction of MoS<inf>2</inf> and WSe<inf>2</inf>. , 2014, , .		4
56	Exfoliated multilayer MoTe2 field-effect transistors. Applied Physics Letters, 2014, 105, .	3.3	168
57	Electronic transport properties of top-gated epitaxial-graphene nanoribbon field-effect transistors on SiC wafers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 012202.	1.2	4
58	Continuous semiempirical model for the current-voltage characteristics of tunnel fets. , 2014, , .		24
59	Investigation of aging and restoration of polyethylene-oxide cesium-perchlorate solid polymer electrolyte used for ion doping of a WSe<inf>2</inf> field-effect transistor. , 2014, , .		1
60	Tunnel Field-Effect Transistors: State-of-the-Art. IEEE Journal of the Electron Devices Society, 2014, 2, 44-49.	2.1	511
61	Optimum Bandgap and Supply Voltage in Tunnel FETs. IEEE Transactions on Electron Devices, 2014, 61, 2719-2724.	3.0	17
62	Electronics based on two-dimensional materials. Nature Nanotechnology, 2014, 9, 768-779.	31.5	2,505
63	High-voltage field effect transistors with wide-bandgap Î²-Ga2O3 nanomembranes. Applied Physics Letters, 2014, 104, .	3.3	288
64	Tunnel transistors. , 2014, , 117-143.		1
65	Direct Measurement of Dirac Point Energy at the Graphene/Oxide Interface. Nano Letters, 2013, 13, 131-136.	9.1	67
66	The Tunneling Transistor. IEEE Spectrum, 2013, 50, 35-62.	0.7	30
67	Exfoliated MoTe<inf>2</inf> field-effect transistor. , 2013, , .		3
68	A unique photoemission method to measure semiconductor heterojunction band offsets. Applied Physics Letters, 2013, 102, 012101.	3.3	11
69	Comparative study of chemically synthesized and exfoliated multilayer MoS2 field-effect transistors. Applied Physics Letters, 2013, 102, 043116.	3.3	35
70	Novel logic devices based on 2D crystal semiconductors: Opportunities and challenges. , 2013, , .		0
71	Tunnel FETs with tunneling normal to the gate. , 2013, , .		1
72	Nanomembrane β-Ga<inf>2</inf>O<inf>3</inf> high-voltage field effect transistors. , 2013, , .		1

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73	Graphene as transparent electrode for direct observation of hole photoemission from silicon to oxide. Applied Physics Letters, 2013, 102, .	3.3	24
74	Bistable-Body Tunnel SRAM. IEEE Nanotechnology Magazine, 2012, 11, 1067-1072.	2.0	7
75	Fabrication of top-gated epitaxial graphene nanoribbon FETs using hydrogen-silsesquioxane. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	1.2	18
76	Tunnel field-effect transistor heterojunction band alignment by internal photoemission spectroscopy. Applied Physics Letters, 2012, 100, .	3.3	15
77	InGaAs/InP Tunnel FETs With a Subthreshold Swing of 93 mV/dec and $I_{m ON}/I_{m OFF}$ Ratio Near $hbox{10}^{6}$. IEEE Electron Device Letters, 2012, 33, 782-784.	3.9	81
78	Novel gate-recessed vertical InAs/GaSb TFETs with record high I<inf>ON</inf> of 180 μA/μm at V<inf>DS</inf> = 0.5 V. , 2012, , .		54
79	First demonstration of two-dimensional WS<inf>2</inf> transistors exhibiting 10⁵ room temperature modulation and ambipolar behavior. , 2012, , .		2
80	Influence of Fe₂O₃ Nanofiller Shape on the Conductivity and Thermal Properties of Solid Polymer Electrolytes: Nanorods versus Nanospheres. Journal of Physical Chemistry C, 2012, 116, 21216-21223.	3.1	69
81	Perspectives of TFETs for low power analog ICs. , 2012, , .		17
82	Transistors with chemically synthesized layered semiconductor WS2 exhibiting 105 room temperature modulation and ambipolar behavior. Applied Physics Letters, 2012, 101, .	3.3	237
83	Frequency response of LaAlO3/SrTiO3 all-oxide field-effect transistors. Solid-State Electronics, 2012, 76, 1-4.	1.4	10
84	Transport properties of graphene nanoribbon transistors on chemical-vapor-deposition grown wafer-scale graphene. Applied Physics Letters, 2012, 100, .	3.3	55
85	InAs/AlGaSb heterojunction tunnel fieldâ€effect transistor with tunnelling inâ€line with the gate field. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 389-392.	0.8	39
86	Determination of graphene work function and graphene-insulator-semiconductor band alignment by internal photoemission spectroscopy. Applied Physics Letters, 2012, 101, .	3.3	166
87	AlGaSb/InAs Tunnel Field-Effect Transistor With On-Current of 78 $muhbox{A}/muhbox{m}$ at 0.5 V. IEEE Electron Device Letters, 2012, 33, 363-365.	3.9	129
88	Performance of AlGaSb/InAs TFETs With Gate Electric Field and Tunneling Direction Aligned. IEEE Electron Device Letters, 2012, 33, 655-657.	3.9	103
89	The MoS2 Nanotubes with Defect-Controlled Electric Properties. Nanoscale Research Letters, 2011, 6, 26.	5.7	71
90	Fundamentals and current status of steep-slope tunnel field-effect transistors. , 2011, , .		0

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91	Band alignment of TFET heterojunctions and post deposition annealing effects by internal photoemission spectroscopy. , 2011, , .		0
92	Fundamentals and current status of steep-slope tunnel field-effect transistors. , 2011, , .		3
93	Sub-10 nm epitaxial graphene nanoribbon FETs. , 2011, , .		2
94	Vertical InGaAs/InP Tunnel FETs With Tunneling Normal to the Gate. IEEE Electron Device Letters, 2011, 32, 1516-1518.	3.9	57
95	Self-aligned InAs/Al<inf>0.45</inf>Ga<inf>0.55</inf>Sb vertical tunnel FETs. , 2011, , .		12
96	(Invited) III-V Tunnel Field-Effect Transistors. ECS Transactions, 2011, 41, 227-229.	0.5	3
97	InAlAs/InGaAs Interband Tunnel Diodes for SRAM. IEEE Transactions on Electron Devices, 2010, 57, 2587-2593.	3.0	4
98	Device and Architecture Outlook for Beyond CMOS Switches. Proceedings of the IEEE, 2010, 98, 2169-2184.	21.3	258
99	Low-Voltage Tunnel Transistors for Beyond CMOS Logic. Proceedings of the IEEE, 2010, 98, 2095-2110.	21.3	1,362
100	Tunnel field-effect transistors - status and prospects. , 2010, , .		4
101	Fabrication approach for lateral InGaAs tunnel transistors. , 2009, , .		0
102	Field modulation in heavily-doped thin-body p+InGaAs for tunnel FETs. , 2009, , .		0
103	Fully-depleted Ge interband tunnel transistor: Modeling and junction formation. Solid-State Electronics, 2009, 53, 30-35.	1.4	53
104	Deposition of HfO2 on InAs by atomic-layer deposition. Microelectronic Engineering, 2009, 86, 1561-1563.	2.4	39
105	One-transistor bistable-body tunnel SRAM. , 2009, , .		8
106	Graphene Nanoribbon Tunnel Transistors. IEEE Electron Device Letters, 2008, 29, 1344-1346.	3.9	193
107	Growth of InAs on Si substrates at low temperatures using metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2008, 310, 4772-4775.	1.5	11
108	Structural Sensitivity of Interband Tunnel Diodes for SRAM. , 2008, , .		5

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109	Record PVCR GaAs-based tunnel diodes fabricated on Si substrates using aspect ratio trapping. , 2008, , .		12
110	InAs film grown on Si(111) by metal organic vapor phase epitaxy. Journal of Physics: Conference Series, 2008, 100, 042017.	0.4	10
111	Effect of surface pretreatment and substrate orientation on the characteristics of InAs quantum dots on Si and SiO[sub 2] substrates. Journal of Vacuum Science & Technology B, 2007, 25, 945.	1.3	2
112	Characterization and control of unconfined lateral diffusion under stencil masks. Journal of Vacuum Science & Technology B, 2007, 25, 857.	1.3	20
113	Rapid Melt Growth of Germanium Tunnel Junctions. Journal of the Electrochemical Society, 2007, 154, H536.	2.9	3
114	Rapid melt growth of Ge tunnel junctions for interband tunnel transistors. , 2007, , .		1
115	Electrical properties of HfO<inf>2</inf>/InAs MOS capacitors. , 2007, , .		2
116	InAs growth on submicron (100) SOI islands for InAs-Si composite channel MOSFETs. , 2007, , .		0
117	W₅O₁₄ Nanowires. Advanced Functional Materials, 2007, 17, 1974-1978.	14.9	77
118	Low-subthreshold-swing tunnel transistors. IEEE Electron Device Letters, 2006, 27, 297-300.	3.9	533
119	Influence of uniaxial tensile strain on the performance of partially depleted SOI CMOS ring oscillators. IEEE Electron Device Letters, 2006, 27, 52-54.	3.9	3
120	Impact of uniaxial strain on the gate leakage currents of PD-SOI MOSFETs and ring oscillators with ultra-thin gate dielectric. , 2005, , .		0
121	Opposing dependence of the electron and hole gate currents in SOI MOSFETs under uniaxial strain. IEEE Electron Device Letters, 2005, 26, 410-412.	3.9	51
122	A Combined Chemical Vapor Deposition and Rapid Thermal Diffusion Process for SiGe Esaki Diodes by Ultra-Shallow Junction Formation. IEEE Nanotechnology Magazine, 2005, 4, 594-598.	2.0	8
123	Design approach using tunnel diodes for lowering power in differential comparators. IEEE Transactions on Circuits and Systems Part 2: Express Briefs, 2005, 52, 572-575.	2.2	7
124	Analytic expression and approach for low subthreshold-swing tunnel transistors. , 2005, , .		7
125	TUNNEL DIODE/TRANSISTOR DIFFERENTIAL COMPARATOR. , 2005, , .		0
126	SiGe Esaki tunnel diodes fabricated by UHV-CVD growth and proximity rapid thermal diffusion. Electronics Letters, 2004, 40, 83.	1.0	11

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127	Nanofabrication using nanotranslated stencil masks and lift off. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 74.	1.6	18
128	TUNNEL DIODE/TRANSISTOR DIFFERENTIAL COMPARATOR. International Journal of High Speed Electronics and Systems, 2004, 14, 640-645.	0.7	0
129	Partially Depleted SOI MOSFETs Under Uniaxial Tensile Strain. IEEE Transactions on Electron Devices, 2004, 51, 317-323.	3.0	65
130	Unified AC model for the resonant tunneling diode. IEEE Transactions on Electron Devices, 2004, 51, 653-657.	3.0	49
131	Silicon tunnel diodes formed by proximity rapid thermal diffusion. IEEE Electron Device Letters, 2003, 24, 93-95.	3.9	25
132	Disorder-effects in reduced dimensional and quantum electronics. AIP Conference Proceedings, 2001, , .	0.4	0
133	Irradiation effects in InGaAs/InAlAs high electron mobility transistors. Applied Physics Letters, 2001, 79, 2279-2281.	3.3	8
134	Epitaxial Si-based tunnel diodes. Thin Solid Films, 2000, 380, 145-150.	1.8	16
135	Current-voltage characteristics of high current density silicon Esaki diodes grown by molecular beam epitaxy and the influence of thermal annealing. IEEE Transactions on Electron Devices, 2000, 47, 1707-1714.	3.0	47
136	MeV ion-induced suppression of resonance current in InP-based resonant tunneling diodes. Applied Physics Letters, 2000, 76, 2562-2564.	3.3	5
137	Disorder effects in reduced dimension: Indiumâ€“phosphide-based resonant tunneling diodes. Journal of Applied Physics, 2000, 88, 6951-6953.	2.5	8
138	Epitaxially grown Si resonant interband tunnel diodes exhibiting high current densities. IEEE Electron Device Letters, 1999, 20, 329-331.	3.9	30
139	Proton-induced disorder in InP-based resonant tunneling diodes. Applied Physics Letters, 1999, 75, 280-282.	3.3	6
140	Ionization and displacement damage irradiation studies of quantum devices: resonant tunneling diodes and two-dimensional electron gas transistors. IEEE Transactions on Nuclear Science, 1999, 46, 1702-1707.	2.0	5
141	Si resonant interband tunnel diodes grown by low-temperature molecular-beam epitaxy. Applied Physics Letters, 1999, 75, 1308-1310.	3.3	29
142	Resonant-tunneling mixed-signal circuit technology. Solid-State Electronics, 1999, 43, 1355-1365.	1.4	30
143	Multibit resonant tunneling diode SRAM cell based on slew-rate addressing. IEEE Transactions on Electron Devices, 1999, 46, 55-62.	3.0	24
144	Special Issue On Quantum Devices And Their Applications. Proceedings of the IEEE, 1999, 87, 535-536.	21.3	6

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145	Evaluating the minimum thickness of gate oxide on silicon using first-principles method. Applied Surface Science, 1998, 135, 137-142.	6.1	61
146	A monolithic 4-bit 2-Gsps resonant tunneling analog-to-digital converter. IEEE Journal of Solid-State Circuits, 1998, 33, 1342-1349.	5.4	202
147	Room temperature operation of epitaxially grown Si/Si0.5Ge0.5/Si resonant interband tunneling diodes. Applied Physics Letters, 1998, 73, 2191-2193.	3.3	104
148	RTD/HFET low standby power SRAM gain cell. IEEE Electron Device Letters, 1998, 19, 7-9.	3.9	97
149	Resonant tunneling in disordered materials such as SiO/sub 2//Si/SiO/sub 2/. , 1997, , .		0
150	Nonparabolicity effects in the bipolar quantum-well resonant-tunneling transistor. Physical Review B, 1997, 55, 7068-7072.	3.2	4
151	A monolithic 4 bit 2 GSps resonant tunneling analog-to-digital converter. , 1997, , .		17
152	Ultralow current density RTDs for tunneling-based SRAM. , 1997, , .		4
153	Beyond-The-Roadmap Technology: Silicon Heterojunctions, Optoelectronics, and Quantum Devices. Materials Research Society Symposia Proceedings, 1997, 486, 67.	0.1	3
154	Controlled growth of SiO2 tunnel barrier and crystalline Si quantum wells for Si resonant tunneling diodes. Journal of Applied Physics, 1997, 81, 6415-6424.	2.5	37
155	Band Offset Measurement Of The ZnS/Si[001] Heterojunction. , 1997, , .		2
156	Potential nanoelectronic integrated circuit technologies. Microelectronic Engineering, 1996, 32, 15-30.	2.4	12
157	Void formation on ultrathin thermal silicon oxide films on the Si(100) surface. Applied Physics Letters, 1996, 69, 1270-1272.	3.3	77
158	Minority carrier magnetoâ€oscillations in the bipolar quantum well resonant tunneling transistor. Journal of Applied Physics, 1996, 79, 2732-2737.	2.5	1
159	Direct extraction of the electron tunneling effective mass in ultrathin SiO2. Applied Physics Letters, 1996, 69, 2728-2730.	3.3	258
160	Functional InP/InGaAs lateral double barrier heterostructure resonant tunneling diodes by using etch and regrowth. Applied Physics Letters, 1996, 69, 1918-1920.	3.3	2
161	Fabrication of lateral resonant tunneling devices with heterostructure barriers. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1996, 14, 4038.	1.6	0
162	Interface characterization of an InP/InGaAs resonant tunneling diode by scanning tunneling microscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 602-606.	2.1	18

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164	Interface characterization in an InP/InGaAs resonant tunneling diode by scanning tunneling microscopy. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 660.	1.6	17
165	Improved turn-on characteristics of a hot electron transistor at 300 K. IEEE Electron Device Letters, 1994, 15, 409-411.	3.9	3
166	Roomâ€temperature operation of a tunneling hotâ€electron transfer amplifier. Applied Physics Letters, 1994, 64, 1138-1140.	3.3	10
167	The use of organometallic group-V sources for the metalorganic molecular beam epitaxy growth of In0.48Ga0.52P/GaAs and In0.53Ga0.47As/InP heterojunction bipolar device structures. Journal of Crystal Growth, 1994, 136, 1-10.	1.5	14
168	Coupled-quantum-well field-effect resonant tunneling transistor for multi-valued logic/memory applications. IEEE Transactions on Electron Devices, 1994, 41, 132-137.	3.0	13
169	Integration of resonant-tunneling transistors and hot-electron transistors. IEEE Electron Device Letters, 1994, 15, 254-256.	3.9	6
170	Resonant-Tunneling Transistors. Edpacs, 1994, , 351-383.	1.0	8
171	Prospects for Semiconductor Quantum Devices. Advances in Chemistry Series, 1994, , 15-42.	0.6	4
172	Atomic layer epitaxy for resonant tunneling devices. Thin Solid Films, 1993, 225, 99-104.	1.8	10
173	Observation of resonant tunneling at room temperature in GaInP/GaAs/GaInP double-heterojunction bipolar transistor. IEEE Transactions on Electron Devices, 1993, 40, 1384-1389.	3.0	18
174	Room-temperature operation of InGaAs-based hot-electron transistors. IEEE Transactions on Electron Devices, 1993, 40, 2134.	3.0	0
175	Co-integration of resonant tunneling and double heterojunction bipolar transistors on InP. IEEE Electron Device Letters, 1993, 14, 472-474.	3.9	28
176	Room-temperature operation of a resonant-tunneling hot-electron transistor based integrated circuit. IEEE Electron Device Letters, 1993, 14, 441-443.	3.9	18
177	Room-temperature resonant tunnelling bipolar transistor XNOR and XOR integrated circuits. Electronics Letters, 1993, 29, 1802.	1.0	25
178	Resonant Tunneling Transistors. , 1993, , .		0
179	Fabrication of lateral resonant tunneling devices. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1992, 10, 2941.	1.6	3
180	Hysteresis in resonant tunneling diode based multiple-peak driver device for multivalued SRAM cells: analysis, simulation, and experimental results. Canadian Journal of Physics, 1992, 70, 993-1000.	1.1	9

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181	Nine-state resonant tunneling diode memory. IEEE Electron Device Letters, 1992, 13, 479-481.	3.9	107
182	The use of tertiarybutylphosphine and tertiarybutylarsine for the metalorganic molecular beam epitaxy of the In0.53Ga0.47As/InP and In0.48Ga0.52P/GaAs materials systems. Journal of Crystal Growth, 1992, 116, 436-446.	1.5	55
183	The Use of Tertiarybutylphosphine and Tertiarybutylarsine for the Metalorganic Molecular Beam Epitaxial Growth of Resonant Tunneung Devices. Materials Research Society Symposia Proceedings, 1991, 240, 33.	0.1	6
184	In0.52Al0.48As/In0.53Ga0.47As lateral resonant tunnelling transistor. Electronics Letters, 1991, 27, 1832.	1.0	13
185	Room Temperature Hot Electron Transistors with InAs-Notched Resonant-Tunneling-Diode Injector. Japanese Journal of Applied Physics, 1991, 30, 921-925.	1.5	30
186	Resonant transmission in the base/collector junction of a bipolar quantumâ€well resonantâ€tunneling transistor. Applied Physics Letters, 1991, 59, 3413-3415.	3.3	22
187	Formation of rotationâ€induced superlattices and their observation by tunneling spectroscopy. Applied Physics Letters, 1991, 59, 570-572.	3.3	0
188	Electric field coupling to quantum dot diodes. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2893.	1.6	7
189	<title>Advances in the processing of quantum-coupled devices</title>. , 1990, , .		6
190	Semiconductor Resonant Tunneling Device Physics and Applications. Materials Research Society Symposia Proceedings, 1990, 198, 309.	0.1	0
191	Is Resonant Tunneling Transistor a Reality?. Physics Today, 1990, 43, 132-132.	0.3	3
192	Improved MBE Growth Of InGaAs-InAlAs Heterostructures For High-Performance Device Applications. Proceedings of SPIE, 1989, , .	0.8	9
193	Realization of a threeâ€terminal resonant tunneling device: The bipolar quantum resonant tunneling transistor. Applied Physics Letters, 1989, 54, 1034-1036.	3.3	120
194	Quantitative resonant tunneling spectroscopy: Currentâ€voltage characteristics of precisely characterized resonant tunneling diodes. Applied Physics Letters, 1989, 54, 1256-1258.	3.3	31
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